

# LSF010x 适用于开漏和推挽应用的 1/2/8 通道双向多电压电平转换器

## 1 特性

- 用无方向引脚提供双向电压转换
- 容性负载  
≤ 30pF 时，最高支持 100MHz 的升压转换和 100MHz 以上的降压转换；容性负载为 50pF 时，最高支持 40MHz 的升压/降压转换
- 支持热插入
- 可实现以下电压之间的双向电压电平转换
  - 0.95V ↔ 1.8/2.5/3.3/5 V
  - 1.2V ↔ 1.8/2.5/3.3/5V
  - 1.8V ↔ 2.5/3.3/5V
  - 2.5V ↔ 3.3/5V
  - 3.3V ↔ 5V
- 低待机电流
- 支持 TTL 的 5V 耐受 I/O 端口
- 低导通电阻 (Ron) 提供较少的信号失真
- 针对 EN 为低电平的高阻抗 I/O 引脚
- 直通引脚分配以简化印刷电路板 (PCB) 走线路由
- 锁断性能超过了 100mA，符合 JESD 17 规范
- -40°C 至 125°C 工作温度范围
- 静电放电 (ESD) 性能测试符合 JESD 22 规范
  - 2000V 人体放电模式 (A114-B, II 类)
  - 200V 机器放电模式 (A115-A)
  - 1000V 组件充电模式 (C101)

## 2 应用

- G  
P  
I  
O  
,
- MDIO, PMBus, SMBus, SDIO, UART, I<sup>2</sup>C, 和其他电信基础设施中的接口
- 工业用
- 汽车用
- 个人计算

## 3 说明

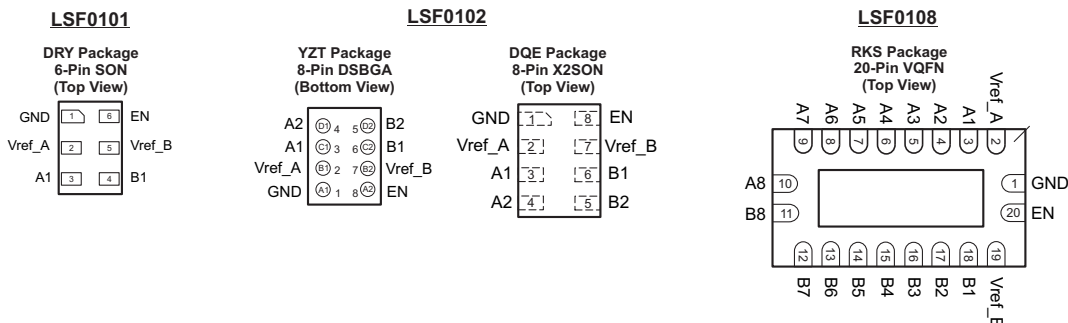
LSF 系列在容性负载 ≤ 30pF 时最高支持 100MHz 的升压转换和 100MHz 以上的降压转换；在容性负载为 50pF 时最高支持 40MHz 的升压/降压转换，因此可支持更多的消费类或电信接口 (MDIO 或 SDIO)。LSF 系列支持双向电压转换，而且无需使用 DIR 引脚，最大限度降低了系统工作量 (PMBus、I<sup>2</sup>C 或 SMBus)。

LSF 系列的 IO 端口能够耐受 5V 电压，因此与工业和电信应用中的 TTL 电平兼容。LSF 系列极具灵活性，能够为每条通道设置不同电压转换电平。

器件信息<sup>(1)</sup>

器件型号	封装 (引脚)	封装尺寸 (标称值)
LSF0101	小外形尺寸无引线 (SON) (6)	1.45mm x 1.00mm
LSF0102	X2SON (8)	1.40mm x 1.00mm
	DSBGA (8)	1.90mm x 1.00mm
	SM8 (8)	2.80mm x 2.95mm
	超薄小外形尺寸封装 (VSSOP)(8)	2.30mm x 2.00mm
LSF0108	超薄四方扁平无引线封装 (VQFN) (20)	4.50mm x 2.50mm
	TSSOP (20)	4.40mm x 6.50mm

(1) 要了解所有可用封装，请参见数据表末尾的可订购产品附录。



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## 4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

<b>Changes from Revision F (October 2015) to Revision G</b>	<b>Page</b>
• 已在“器件信息”表中添加所有可用封装尺寸并已更改引脚图 说明。 .....	<b>1</b>

<b>Changes from Revision E (July 2015) to Revision F</b>	<b>Page</b>
• 已更改 特性 从“支持 100MHz 以上的高速转换”改为“容性负载 $\leq 30\text{pF}$ 时，支持最高 100MHz 的升压转换和 100MHz 以上的降压转换；容性负载为 50pF 时，支持最高 40MHz 的升压/降压转换。” .....	<b>1</b>
• Updated all propagation delay tables changed from generic to specific LSF devices. ....	<b>7</b>

<b>Changes from Revision D (October 2014) to Revision E</b>	<b>Page</b>
• 已删除 特性中的“最大传播延迟低于 1.5ns”。 .....	<b>1</b>
• Updated ESD Ratings table. ....	<b>5</b>
• Increased MAX value for $T_A$ , Operating free-air temperature, from 85°C to 125°C. ....	<b>5</b>

<b>Changes from Revision C (May 2014) to Revision D</b>	<b>Page</b>
• 已将双向电压电平转换从 1.0 改为 0.95 .....	<b>1</b>
• 已更改 已更改 YZT 封装以修正视图错误。 .....	<b>1</b>
• Changed YZT package to fix view error. ....	<b>3</b>
• Added pin numbers to <i>Pin Functions</i> table.....	<b>4</b>
• Added Vref_A footnote. ....	<b>13</b>

**Changes from Revision B (May 2014) to Revision C** **Page**

- 已将 LSF0108 状态由“产品预览”改为“量产数据”。 ..... 1
- 已更新文档标题..... 1
- Updated Handling Ratings table. .... 5

**Changes from Revision A (January 2014) to Revision B** **Page**

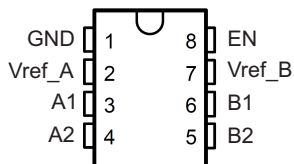
- 在数据表中添加了 LSF0108。 ..... 1

**Changes from Original (December 2013) to Revision A** **Page**

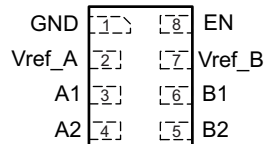
- 已更新产品型号。 ..... 1
- Updated *Electrical Characteristics* table..... 6

## 5 Pin Configuration and Functions

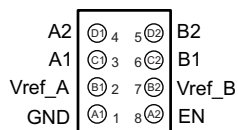
**LSF0102 DCT or DCU Package**  
8-Pin SM8 or VSSOP  
Top View



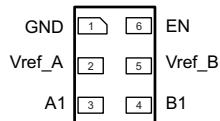
**LSF0102 DQE Package**  
8-Pin X2SON  
Top View



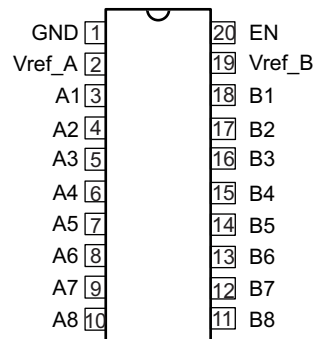
**LSF0102 YZT Package**  
8-Pin DSBGA  
Bottom View



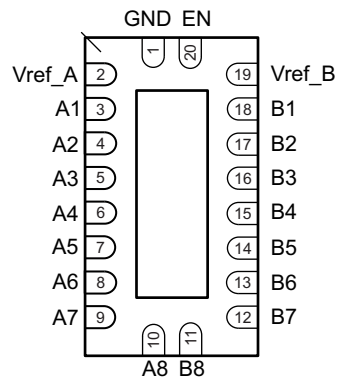
**LSF0101 DRY Package**  
6-Pin SON  
Top View



**LSF0108 PW Package  
20-Pin TSSOP  
Top View**



**LSF0108 RKS Package  
20-Pin VQFN  
Top View**



**Pin Functions**

NAME	PIN			DESCRIPTION
	DCT, DCU, DQE, YZT NO.	DRY NO.	PW or RKS NO.	
An	3, 4	3	3 to 10	Data port
Bn	6, 5	4	18 to 11	
EN	8	6	20	Switch enable input; connect to Vref_B and pull-up through a high resistor (200 kΩ).
GND	1	1	1	Ground
Vref_A	2	2	2	Reference supply voltage; see <a href="#">Application and Implementation</a> .
Vref_B	7	5	19	Reference supply voltage; see <a href="#">Application and Implementation</a> .

## 6 Specifications

### 6.1 Absolute Maximum Ratings<sup>(1)</sup>

over operating free-air temperature (unless otherwise noted)

		MIN	MAX	UNIT
$V_I$	Input voltage <sup>(2)</sup>	-0.5	7	V
$V_{I/O}$	Input/output voltage <sup>(2)</sup>	-0.5	7	V
	Continuous channel current		128	mA
$I_{IK}$	Input clamp current	$V_I < 0$	-50	mA
$R_{\theta JA}$	Package thermal impedance <sup>(3)</sup>	DCT package	220	°C/W
		DCU package	227	
$T_{stg}$	Storage temperature range	-65	150	°C

- (1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and input/output negative-voltage ratings may be exceeded if the input and input/output clamp-current ratings are observed.
- (3) The package thermal impedance is calculated in accordance with JESD 51-7.

### 6.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±2000
		Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±1000

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 500-V HBM is possible with the necessary precautions.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 250-V CDM is possible with the necessary precautions.

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
$V_{I/O}$	Input/output voltage	0	5	V
$V_{ref\_A/B/EN}$	Reference voltage	0	5	V
$I_{PASS}$	Pass transistor current		64	mA
$T_A$	Operating free-air temperature	-40	125	°C

## 6.4 Thermal Information: LSF0101, LSF0108

THERMAL METRIC <sup>(1)</sup>		LSF0101	LSF0108	LSF0108	UNIT
		DRY (SON)	RKS (VQFN)	PW (TSSOP)	
		6 PINS	20 PINS	20 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	407.0	49.3	106.6	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	285.2	45.9	41.0	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	271.6	20.6	57.6	°C/W
$\Psi_{JT}$	Junction-to-top characterization parameter	113.5	2.5	4.2	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter	271.0	20.6	47.0	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	n/a	3.4	n/a	°C/W

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

## 6.5 Thermal Information: LSF0102

THERMAL METRIC <sup>(1)</sup>		LSF0102	LSF0102	LSF0102	LSF0102	UNIT
		DCU (US8)	DCT (SM8)	DQE (X2SON)	YZT (DSBGA)	
		8 PINS	8 PINS	8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	210.1	189.6	246.5	125.5	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	89.1	119.6	149.1	1.0	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	88.8	102.1	100.0	62.7	°C/W
$\Psi_{JT}$	Junction-to-top characterization parameter	8.3	44.5	17.1	3.4	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter	88.4	101.0	99.8	62.7	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	n/a	n/a	n/a	n/a	°C/W

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

## 6.6 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		MIN	TYP <sup>(1)</sup>	MAX	UNIT
$V_{IK}$	$I_I = -18 \text{ mA}$ , $V_{EN} = 0$				-1.2	V
$I_{IH}$	$V_I = 5 \text{ V}$ , $V_{EN} = 0$				5.0	μA
$I_{CC}$	$V_{ref\_B} = V_{EN} = 5.5 \text{ V}$ , $V_{ref\_A} = 4.5 \text{ V}$ or $1 \text{ V}$ , $I_O = 0$ , $V_I = V_{CC}$ or GND			1		μA
$C_{I(ref\_A/B/EN)}$	$V_I = 3 \text{ V}$ or $0$			11		pF
$C_{io(off)}$	$V_O = 3 \text{ V}$ or $0$ , $V_{EN} = 0$			4.0	6.0	pF
$C_{io(on)}$	$V_O = 3 \text{ V}$ or $0$ , $V_{EN} = 3 \text{ V}$			10.5	12.5	pF
$r_{on}^{(2)}$	$V_I = 0$ , $I_O = 64 \text{ mA}$	$V_{ref\_A} = 3.3 \text{ V}$ ; $V_{ref\_B} = V_{EN} = 5 \text{ V}$		8.0		Ω
		$V_{ref\_A} = 1.8 \text{ V}$ ; $V_{ref\_B} = V_{EN} = 5 \text{ V}$		9.0		
		$V_{ref\_A} = 1.0 \text{ V}$ ; $V_{ref\_B} = V_{EN} = 5 \text{ V}$		10		
	$V_I = 0$ , $I_O = 32 \text{ mA}$	$V_{ref\_A} = 1.8 \text{ V}$ ; $V_{ref\_B} = V_{EN} = 5 \text{ V}$		10		Ω
		$V_{ref\_A} = 2.5 \text{ V}$ ; $V_{ref\_B} = V_{EN} = 5 \text{ V}$		15		
	$V_I = 1.8 \text{ V}$ , $I_O = 15 \text{ mA}$	$V_{ref\_A} = 3.3 \text{ V}$ ; $V_{ref\_B} = V_{EN} = 5 \text{ V}$		9.0		Ω
	$V_I = 1.0 \text{ V}$ , $I_O = 10 \text{ mA}$	$V_{ref\_A} = 1.8 \text{ V}$ ; $V_{ref\_B} = V_{EN} = 3.3 \text{ V}$		18		Ω
$V_I = 0 \text{ V}$ , $I_O = 10 \text{ mA}$	$V_{ref\_A} = 1.0 \text{ V}$ ; $V_{ref\_B} = V_{EN} = 3.3 \text{ V}$		20		Ω	
$V_I = 0 \text{ V}$ , $I_O = 10 \text{ mA}$	$V_{ref\_A} = 1.0 \text{ V}$ ; $V_{ref\_B} = V_{EN} = 1.8 \text{ V}$		30		Ω	

(1) All typical values are at  $T_A = 25^\circ\text{C}$ .

(2) Measured by the voltage drop between the A and B pins at the indicated current through the switch. On-state resistance is determined by the lowest voltage of the two (A or B) pins.

### 6.7 LSF0101/02 AC Performance (Translating Down) Switching Characteristics, $V_{GATE} = 3.3\text{ V}$

over recommended operating free-air temperature range,  $V_{GATE} = 3.3\text{ V}$ ,  $V_{IH} = 3.3\text{ V}$ ,  $V_{IL} = 0$ , and  $V_M = 1.15\text{ V}$  (unless otherwise noted) (see [Figure 2](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$C_L = 50\text{ pF}$		$C_L = 30\text{ pF}$		$C_L = 15\text{ pF}$		UNIT
			TYP	MAX	TYP	MAX	TYP	MAX	
$t_{PLH}$	A or B	B or A	1.1		0.7		0.3		ns
$t_{PHL}$			1.2		0.8		0.4		

### 6.8 LSF0108 AC Performance (Translating Down) Switching Characteristics, $V_{GATE} = 3.3\text{ V}$

over recommended operating free-air temperature range,  $V_{GATE} = 3.3\text{ V}$ ,  $V_{IH} = 3.3\text{ V}$ ,  $V_{IL} = 0$ , and  $V_M = 1.15\text{ V}$  (unless otherwise noted) (see [Figure 2](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$C_L = 50\text{ pF}$		$C_L = 30\text{ pF}$		$C_L = 15\text{ pF}$		UNIT
			TYP	MAX	TYP	MAX	TYP	MAX	
$t_{PLH}$	A or B	B or A	1.9		1.4		0.75		ns
$t_{PHL}$			2		1.5		0.85		

### 6.9 LSF0101/02 AC Performance (Translating Down) Switching Characteristics, $V_{GATE} = 2.5\text{ V}$

over recommended operating free-air temperature range,  $V_{GATE} = 2.5\text{ V}$ ,  $V_{IH} = 2.5\text{ V}$ ,  $V_{IL} = 0$ , and  $V_M = 0.75\text{ V}$  (unless otherwise noted) (see [Figure 2](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$C_L = 50\text{ pF}$		$C_L = 30\text{ pF}$		$C_L = 15\text{ pF}$		UNIT
			TYP	MAX	TYP	MAX	TYP	MAX	
$t_{PLH}$	A or B	B or A	1.2		0.8		0.35		ns
$t_{PHL}$			1.3		1		0.5		

### 6.10 LSF0108 AC Performance (Translating Down) Switching Characteristics, $V_{GATE} = 2.5\text{ V}$

over recommended operating free-air temperature range,  $V_{GATE} = 2.5\text{ V}$ ,  $V_{IH} = 2.5\text{ V}$ ,  $V_{IL} = 0$ , and  $V_M = 0.75\text{ V}$  (unless otherwise noted) (see [Figure 2](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$C_L = 50\text{ pF}$		$C_L = 30\text{ pF}$		$C_L = 15\text{ pF}$		UNIT
			TYP	MAX	TYP	MAX	TYP	MAX	
$t_{PLH}$	A or B	B or A	2		1.45		0.8		ns
$t_{PHL}$			2.1		1.55		0.9		

### 6.11 LSF0101/02 AC Performance (Translating Up) Switching Characteristics, $V_{GATE} = 3.3\text{ V}$

over recommended operating free-air temperature range,  $V_{GATE} = 3.3\text{ V}$ ,  $V_{IH} = 2.3\text{ V}$ ,  $V_{IL} = 0$ ,  $V_T = 3.3\text{ V}$ ,  $V_M = 1.15\text{ V}$  and  $R_L = 300$  (unless otherwise noted) (see [Figure 2](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$C_L = 50\text{ pF}$		$C_L = 30\text{ pF}$		$C_L = 15\text{ pF}$		UNIT
			TYP	MAX	TYP	MAX	TYP	MAX	
$t_{PLH}$	A or B	B or A	1		0.8		0.4		ns
$t_{PHL}$			1		0.9		0.4		

### 6.12 LSF0108 AC Performance (Translating Up) Switching Characteristics, $V_{GATE} = 3.3\text{ V}$

over recommended operating free-air temperature range,  $V_{GATE} = 3.3\text{ V}$ ,  $V_{IH} = 2.3\text{ V}$ ,  $V_{IL} = 0$ ,  $V_T = 3.3\text{ V}$ ,  $V_M = 1.15\text{ V}$  and  $R_L = 300$  (unless otherwise noted) (see [Figure 2](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$C_L = 50\text{ pF}$		$C_L = 30\text{ pF}$		$C_L = 15\text{ pF}$		UNIT
			TYP	MAX	TYP	MAX	TYP	MAX	
$t_{PLH}$	A or B	B or A	2.1		1.55		0.9		ns
$t_{PHL}$			2.2		1.65		1		

### 6.13 LSF0101/02 AC Performance (Translating Up) Switching Characteristics, $V_{GATE} = 2.5\text{ V}$

over recommended operating free-air temperature range,  $V_{GATE} = 2.5\text{ V}$ ,  $V_{IH} = 1.5\text{ V}$ ,  $V_{IL} = 0$ ,  $V_T = 2.5\text{ V}$ ,  $V_M = 0.75\text{ V}$  and  $R_L = 300$  (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$C_L = 50\text{ pF}$		$C_L = 30\text{ pF}$		$C_L = 15\text{ pF}$		UNIT
			TYP	MAX	TYP	MAX	TYP	MAX	
$t_{PLH}$	A or B	B or A	1.1		0.9		0.45		ns
$t_{PHL}$			1.3		1.1		0.6		

### 6.14 LSF0108 AC Performance (Translating Up) Switching Characteristics, $V_{GATE} = 2.5\text{ V}$

over recommended operating free-air temperature range,  $V_{GATE} = 2.5\text{ V}$ ,  $V_{IH} = 1.5\text{ V}$ ,  $V_{IL} = 0$ ,  $V_T = 2.5\text{ V}$ ,  $V_M = 0.75\text{ V}$  and  $R_L = 300$  (unless otherwise noted) (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$C_L = 50\text{ pF}$		$C_L = 30\text{ pF}$		$C_L = 15\text{ pF}$		UNIT
			TYP	MAX	TYP	MAX	TYP	MAX	
$t_{PLH}$	A or B	B or A	1.8		1.35		0.8		ns
$t_{PHL}$			1.9		1.45		0.9		

### 6.15 Typical Characteristics

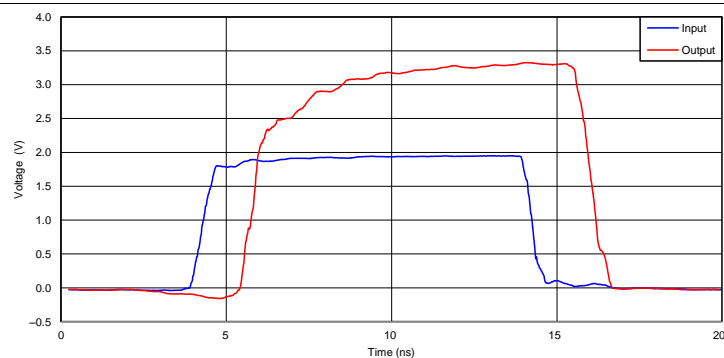
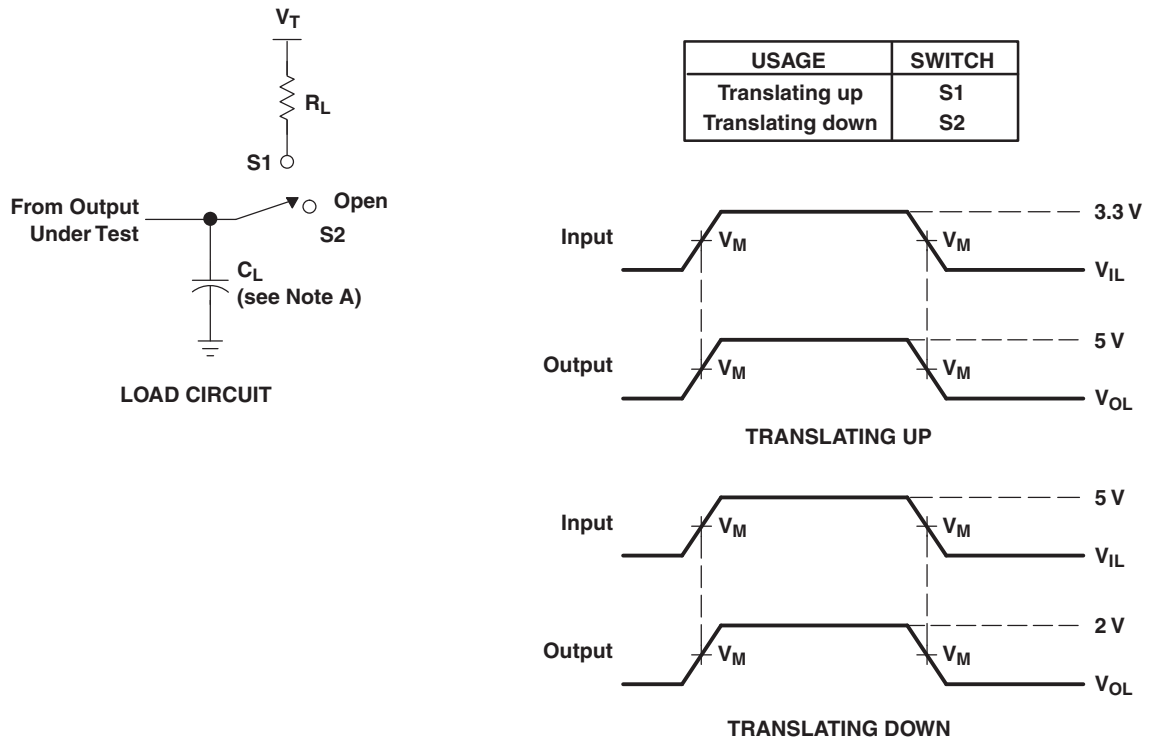


Figure 1. Signal Integrity (1.8 to 3.3 V Translation Up at 50 MHz)



## 7 Parameter Measurement Information



- NOTES: A.  $C_L$  includes probe and jig capacitance.  
 B. All input pulses are supplied by generators having the following characteristics:  $PRR \leq 10\text{ MHz}$ ,  $Z_O = 50\ \Omega$ ,  $t_r \leq 2\text{ ns}$ ,  $t_f \leq 2\text{ ns}$ .  
 C. The outputs are measured one at a time, with one transition per measurement.

**Figure 2. Load Circuit for Outputs**

## 8 Detailed Description

### 8.1 Overview

The LSF family can be used in level translation applications for interfacing devices or systems operating at different interface voltages with one another. The LSF family is ideal for use in applications where an open-drain driver is connected to the data I/Os. With appropriate pull-up resistors and layout, LSF can achieve 100 MHz. The LSF family can also be used in applications where a push-pull driver is connected to the data I/Os.

### 8.2 Functional Block Diagrams

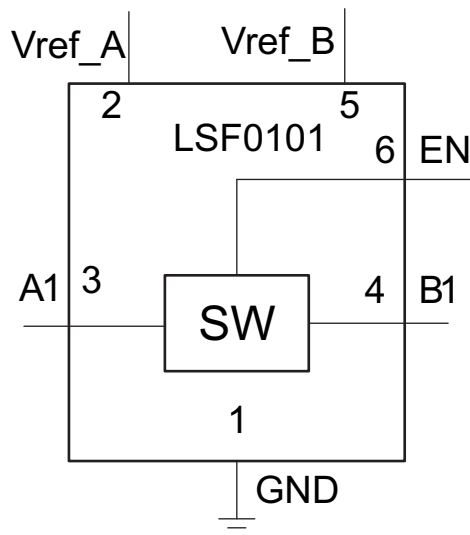


Figure 3. LSF0101 Functional Block Diagram

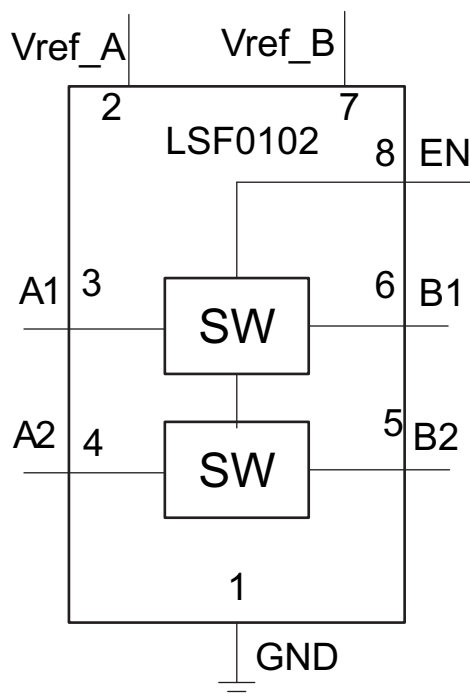


Figure 4. LSF0102 Functional Block Diagram

## Functional Block Diagrams (continued)

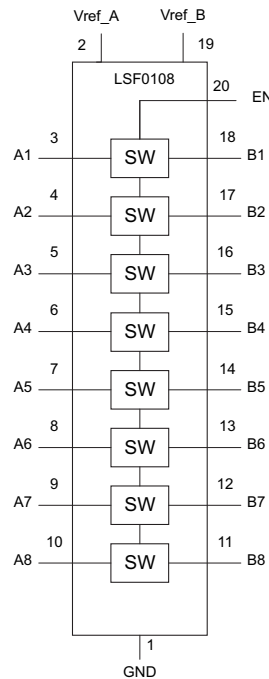


Figure 5. LSF0108 Functional Block Diagram

### 8.3 Feature Description

The LSF family are bidirectional voltage level translators operational from 0.95 to 4.5 V (Vref\_A) and 1.8 to 5.5 V (Vref\_B). This allows bidirectional voltage translations between 1 V and 5 V without the need for a direction pin in open-drain or push-pull applications. LSF family supports level translation applications with transmission speeds greater than 100 Mbps for open-drain systems using a 30-pF capacitance and 250-Ω pullup resistor.

When the An or Bn port is LOW, the switch is in the ON-state and a low resistance connection exists between the An and Bn ports. The low  $R_{on}$  of the switch allows connections to be made with minimal propagation delay and signal distortion. Assuming the higher voltage is on the Bn port when the Bn port is HIGH, the voltage on the An port is limited to the voltage set by Vref\_A. When the An port is HIGH, the Bn port is pulled to the drain pull-up supply voltage ( $V_{pu\#}$ ) by the pull-up resistors. This functionality allows a seamless translation between higher and lower voltages selected by the user without the need for directional control.

The supply voltage ( $V_{pu\#}$ ) for each channel can be individually set up with a pull-up resistor. For example, CH1 can be used in up-translation mode (1.2 V ↔ 3.3 V) and CH2 in down-translation mode (2.5 V ↔ 1.8 V).

When EN is HIGH, the translator switch is on, and the An I/O is connected to the Bn I/O, respectively, allowing bidirectional data flow between ports. When EN is LOW, the translator switch is off, and a high-impedance state exists between ports. The EN input circuit is designed to be supplied by Vref\_B. To ensure the high-impedance state during power-up or power-down, EN must be LOW.

### 8.4 Device Functional Modes

Table 1 expresses the functional modes of the LSF devices.

Table 1. Function Table

INPUT EN <sup>(1)</sup> PIN	FUNCTION
H	An = Bn
L	H-Z

(1) EN is controlled by Vref\_B logic levels and should be at least 1 V higher than Vref\_A for best translator.

## 9 Application and Implementation

### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 9.1 Application Information

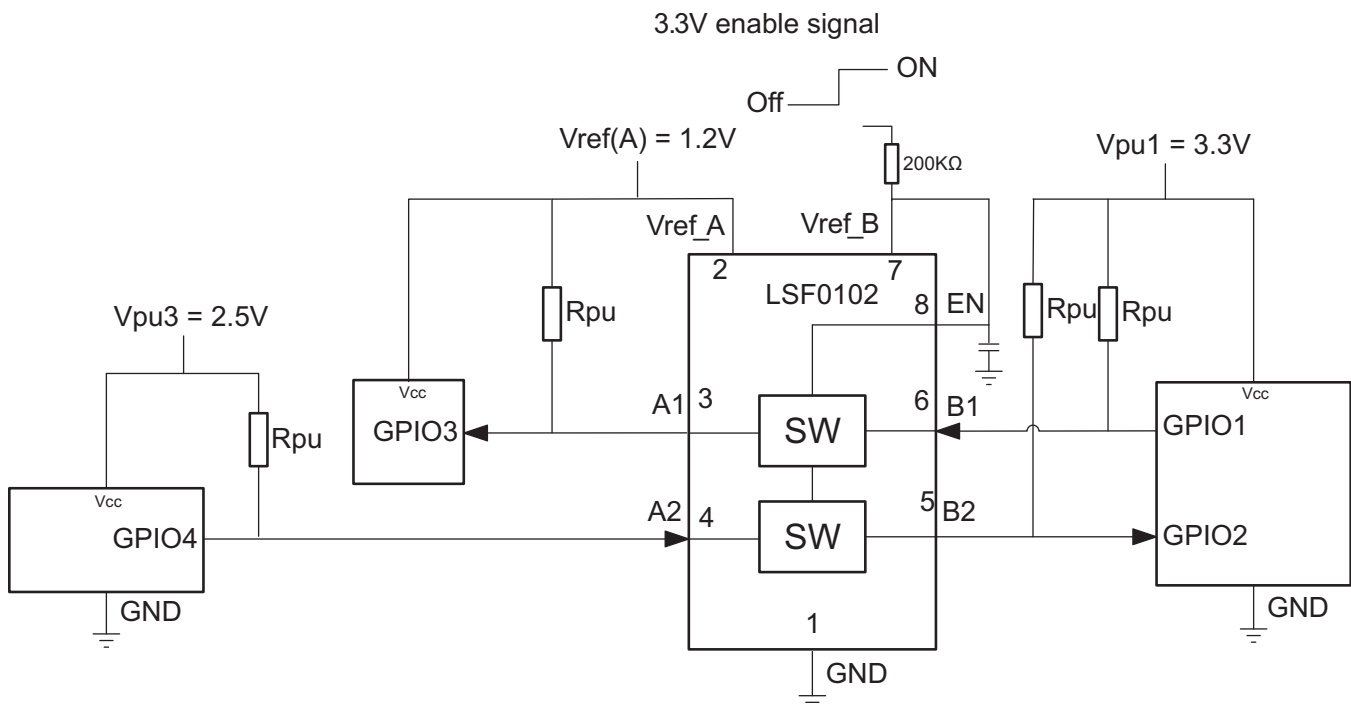
The LSF devices are able to perform voltage translation for open-drain or push-pull interface. [Table 2](#) provides some consumer/telecom interfaces as reference in regards to the different channel numbers that are supported by the LSF family.

**Table 2. Voltage Translator for Consumer/Telecom Interface**

Part Name	Channel Number	Interface
LSF0101	1	GPIO
LSF0102	2	GPIO, MDIO, SMBus, PMBus, I <sup>2</sup> C
LSF0108	8	GPIO, MDIO, SDIO, SVID, UART, SMBus, PMBus, I <sup>2</sup> C, SPI

### 9.2 Typical Application

#### 9.2.1 I<sup>2</sup>C PMBus, SMBus, GPIO



**Figure 6. Bidirectional Translation to Multiple Voltage Levels**

#### 9.2.1.1 Design Requirements

##### 9.2.1.1.1 Enable, Disable, and Reference Voltage Guidelines

The LSF family has an EN input that is used to disable the device by setting EN LOW, which places all I/Os in the high-impedance state. Since LSF family is switch-type voltage translator, the power consumption is very low. It is recommended to always enable LSF family for bidirectional application (I<sup>2</sup>C, SMBus, PMBus, or MDIO).

**Typical Application (continued)**
**Table 3. Application Operating Condition**

PARAMETER		MIN	TYP	MAX	UNIT
Vref_A <sup>(1)</sup>	reference voltage (A)	0.95		4.5	V
Vref_B	reference voltage (B)	Vref_A + 0.8		5.5	V
V <sub>I(EN)</sub>	input voltage on EN pin	Vref_A + 0.8		5.5	V
V <sub>pu</sub>	pull-up supply voltage	0		Vref_B	V

(1) Vref\_A have to be the lowest voltage level across all of inputs and outputs.

**The 200 kΩ, pull-up resistor is required to allow Vref\_B to regulate the EN input.** A filter capacitor on Vref\_B is recommended. Also Vref\_B and V<sub>I(EN)</sub> are recommended to be at 1.0 V higher than Vref\_A for best signal integrity.

**9.2.1.2 Detailed Design Procedure**
**9.2.1.2.1 Bidirectional Translation**

For the bidirectional clamping configuration (higher voltage to lower voltage or lower voltage to higher voltage), the EN input must be connected to Vref\_B and both pins pulled to HIGH side V<sub>pu</sub> through a pull-up resistor (typically 200 kΩ). This allows Vref\_B to regulate the EN input. A filter capacitor on Vref\_B is recommended. The master output driver can be push-pull or open-drain (pull-up resistors may be required) and the slave device output can be push-pull or open-drain (pull-up resistors are required to pull the Bn outputs to V<sub>pu</sub>).

**If either output is push-pull, data must be unidirectional or the outputs must be tri-state and be controlled by some direction-control mechanism to prevent HIGH-to-LOW contentions in either direction. If both outputs are open-drain, no direction control is needed.**

In [Figure 6](#), the reference supply voltage (Vref\_A) is connected to the processor core power supply voltage. When Vref\_B is connected through a 200 kΩ resistor to a 3.3 V V<sub>pu</sub> power supply, and Vref\_A is set 1.0 V. The output of A3 and B4 has a maximum output voltage equal to Vref\_A, and the bidirectional interface (Ch1/2, MDIO) has a maximum output voltage equal to V<sub>pu</sub>.

**9.2.1.2.2 Pull-up Resistor Sizing**

The pull-up resistor value needs to limit the current through the pass transistor when it is in the ON state to about 15 mA. This ensures a pass voltage of 260 mV to 350 mV. If the current through the pass transistor is higher than 15 mA, the pass voltage also is higher in the ON state. To set the current through each pass transistor at 15 mA, to calculate the pull-up resistor value use the following equation:

$$R_{pu} = (V_{pu} - 0.35 \text{ V}) / 0.015 \text{ A} \quad (1)$$

[Table 4](#) summarizes resistor values, reference voltages, and currents at 15 mA, 10 mA, and 3 mA. The resistor value shown in the +10% column (or a larger value) should be used to ensure that the pass voltage of the transistor is 350 mV or less. The external driver must be able to sink the total current from the resistors on both sides of the LSF family device at 0.175 V, although the 15 mA applies only to current flowing through the LSF family device.

**Table 4. Pull-up Resistor Values<sup>(1)(2)</sup>**

V <sub>DPU</sub>	15 mA		10 mA		3 mA	
	NOMINAL (Ω)	+10% <sup>(3)</sup> (Ω)	NOMINAL (Ω)	+10% <sup>(3)</sup> (Ω)	NOMINAL (Ω)	+10% <sup>(3)</sup> (Ω)
5 V	310	341	465	512	1550	1705
3.3 V	197	217	295	325	983	1082
2.5 V	143	158	215	237	717	788
1.8 V	97	106	145	160	483	532
1.5 V	77	85	115	127	383	422
1.2 V	57	63	85	94	283	312

(1) Calculated for V<sub>OL</sub> = 0.35 V

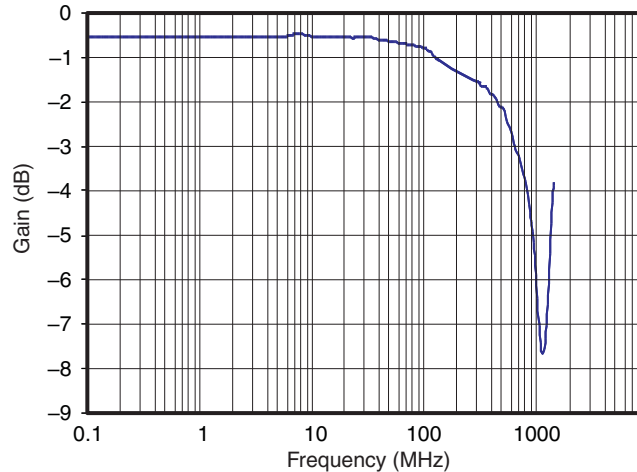
(2) Assumes output driver V<sub>OL</sub> = 0.175 V at stated current

(3) +10% to compensate for V<sub>DD</sub> range and resistor tolerance

### 9.2.1.2.3 LSF Family Bandwidth

The maximum frequency of the LSF family is dependent on the application. The device can operate at speeds of >100 MHz given the correct conditions. The maximum frequency is dependent upon the loading of the application. The LSF family behaves like a standard switch where the bandwidth of the device is dictated by the on resistance and on capacitance of the device.

Figure 7 shows a bandwidth measurement of the LSF family using a two-port network analyzer.



**Figure 7. 3-dB Bandwidth**

The 3-dB point of the LSF family is  $\approx 600$  MHz; however, this measurement is an analog type of measurement. For digital applications the signal should not degrade up to the fifth harmonic of the digital signal. The frequency bandwidth should be at least five times the maximum digital clock rate. This component of the signal is very important in determining the overall shape of the digital signal. In the case of the LSF family, a digital clock frequency of greater than 100 MHz can be achieved.

The LSF family does not provide any drive capability. Therefore higher frequency applications will require higher drive strength from the host side. No pull-up resistor is needed on the host side (3.3 V) if the LSF family is being driven by standard CMOS totem pole output driver. Ideally, it is best to minimize the trace length from the LSF family on the sink side (1.8 V) to minimize signal degradation.

All fast edges have an infinite spectrum of frequency components; however, there is an inflection (or knee) in the frequency spectrum of fast edges where frequency components higher than  $f_{knee}$  are insignificant in determining the shape of the signal.

To calculate the maximum practical frequency component, or the knee frequency ( $f_{knee}$ ), use the following equations:

$$f_{knee} = 0.5 / RT \text{ (10 – 80\%)} \quad (2)$$

$$f_{knee} = 0.4 / RT \text{ (20 – 80\%)} \quad (3)$$

For signals with rise time characteristics based on 10% to 90% thresholds,  $f_{knee}$  is equal to 0.5 divided by the rise time of the signal. For signals with rise time characteristics based on 20% to 80% thresholds, which is very common in many of today's device specifications,  $f_{knee}$  is equal to 0.4 divided by the rise time of the signal.

Some guidelines to follow that will help maximize the performance of the device:

- Keep trace length to a minimum by placing the LSF family close to the I<sup>2</sup>C output of the processor.
- The trace length should be less than half the time of flight to reduce ringing and line reflections or non-monotonic behavior in the switching region.
- To reduce overshoots, a pull-up resistor can be added on the 1.8 V side; be aware that a slower fall time is to be expected.

### 9.2.1.3 Application Curve

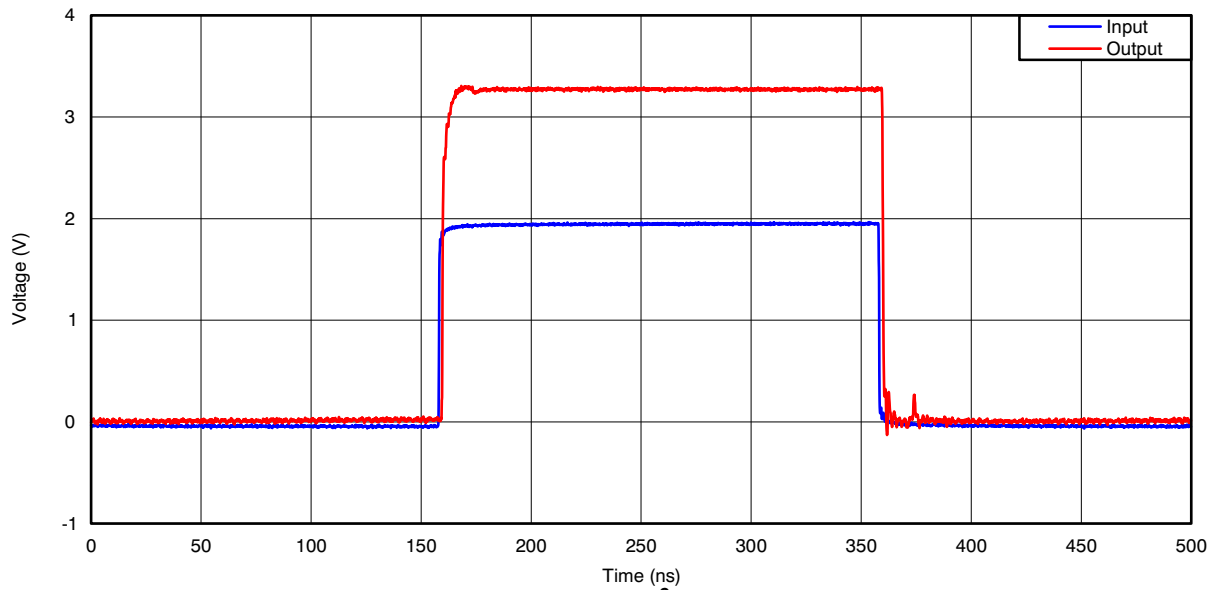


Figure 8. Captured Waveform From Above I<sup>2</sup>C Set-Up (1.8 V to 3.3 V at 2.5 MHz)

9.2.2 MDIO

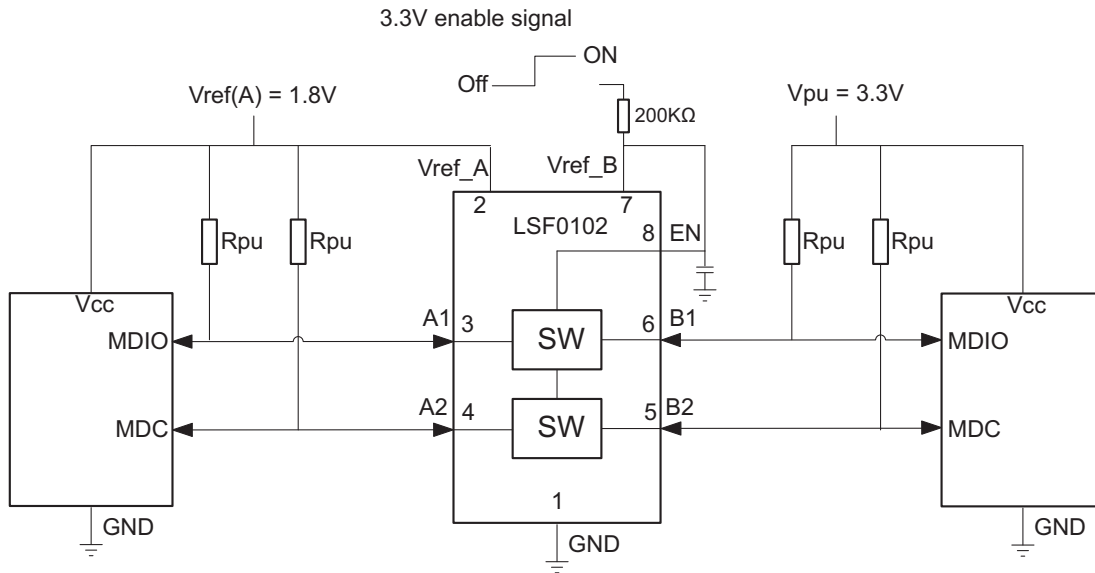


Figure 9. Typical Application Circuit (MDIO/Bidirectional Interface)

9.2.2.1 Design Requirements

Refer to [Design Requirements](#).

9.2.2.2 Detailed Design Procedure

Refer to [Detailed Design Procedure](#).

9.2.2.3 Application Curve

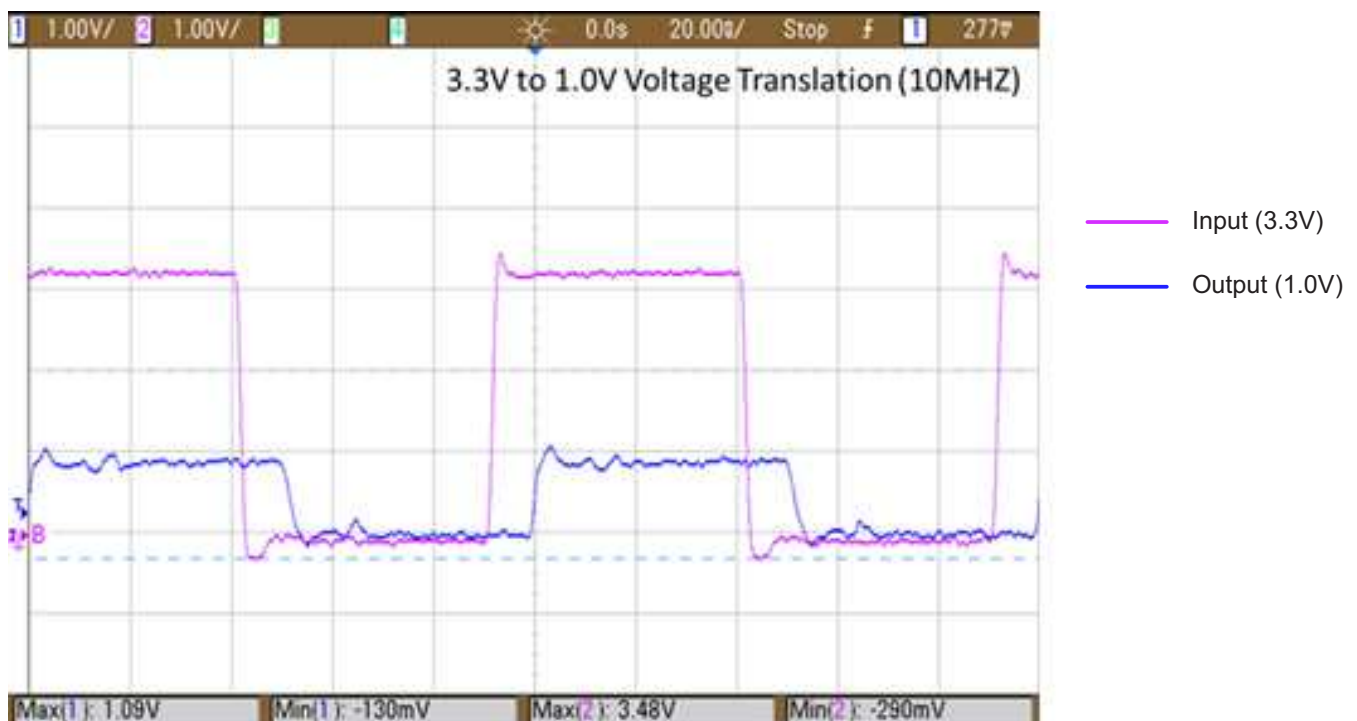
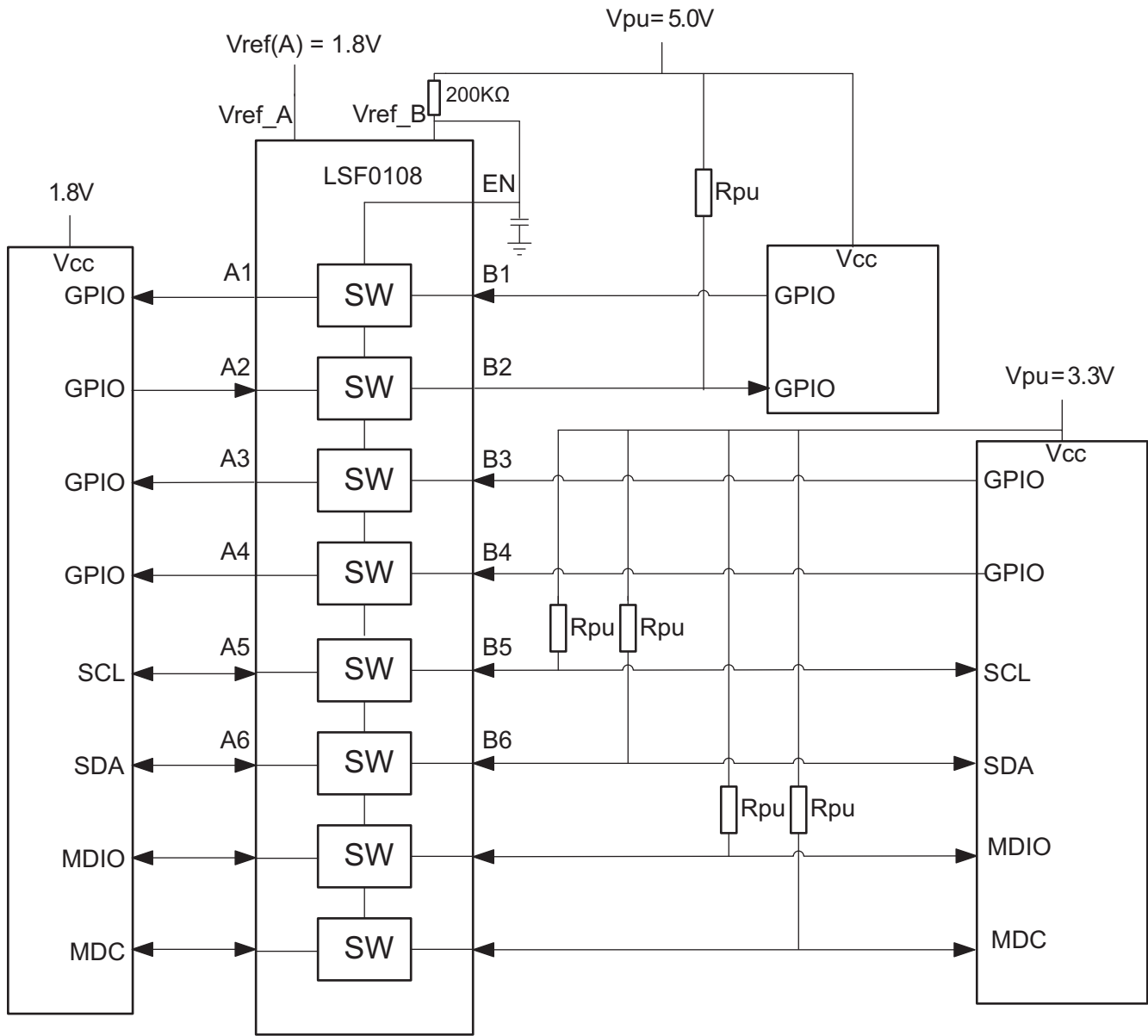


Figure 10. Captured Waveform From Above MDIO Setup



9.2.3 Multiple Voltage Translation in Single Device



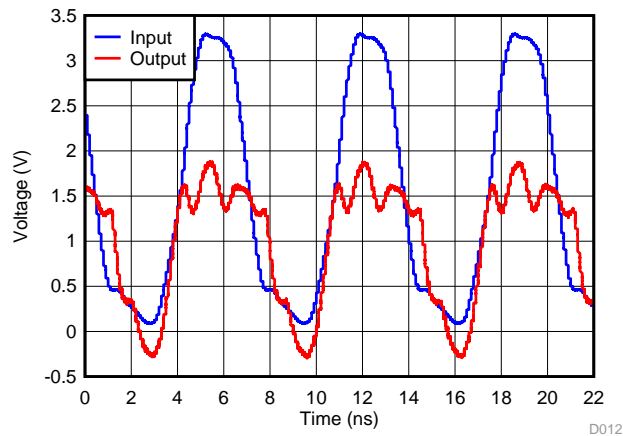
9.2.3.1 Design Requirements

Refer to [Design Requirements](#).

9.2.3.2 Detailed Design Procedure

Refer to [Detailed Design Procedure](#).

**9.2.3.3 Application Curve**



**Figure 11. Translation Down (3.3 to 1.8 V) at 150 MHz**

## 10 Power Supply Recommendations

There are no power sequence requirements for the LSF family. For enable and reference voltage guidelines, please refer to the [Enable, Disable, and Reference Voltage Guidelines](#).

## 11 Layout

### 11.1 Layout Guidelines

Because the LSF family is a switch-type level translator, the signal integrity is highly related with a pull-up resistor and PCB capacitance condition.

- Short signal trace as possible to reduce capacitance and minimize stub from pull-up resistor.
- Place LSF close to high voltage side.
- Select the appropriate pull-up resistor that applies to translation levels and driving capability of transmitter.

### 11.2 Layout Example

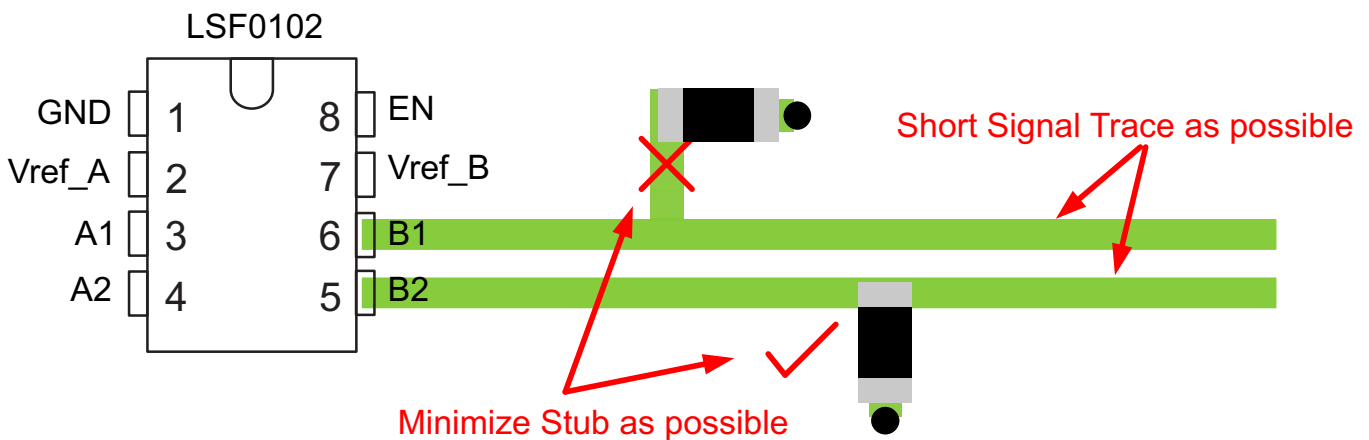


Figure 12. Short Trace Layout

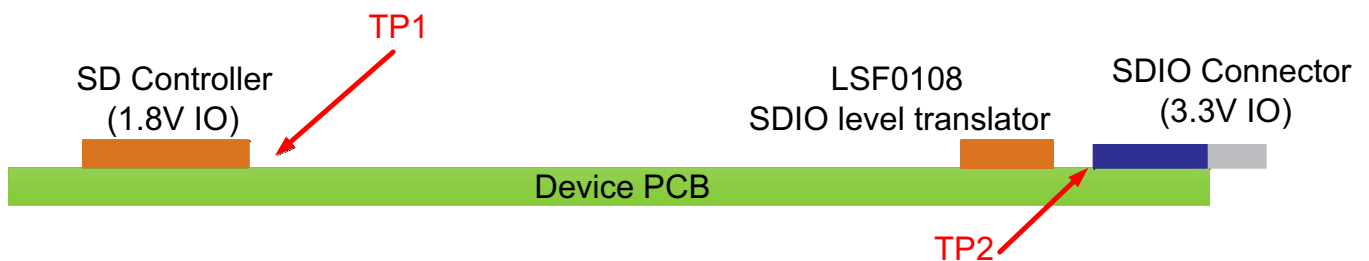
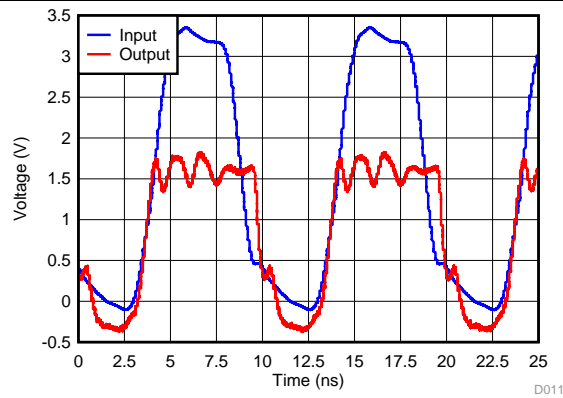
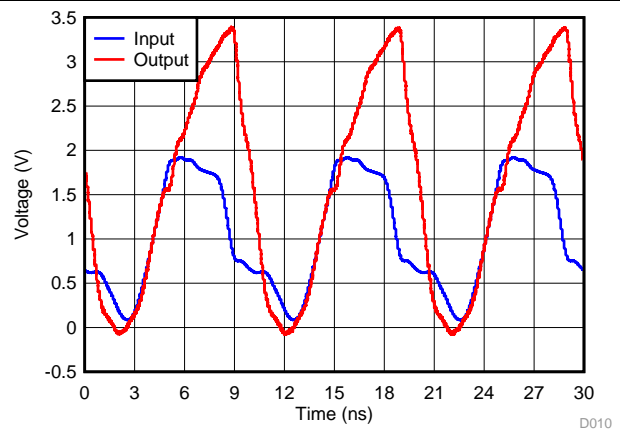


Figure 13. Device Placement

**Layout Example (接下页)**


**Figure 14. Waveform From TP1 (Pull-up Resistor: 160-Ω and 50-pF Capacitance 3.3 V to 1.8 V at 100 MHz)**



**Figure 15. Waveform From TP2 (Pull-up Resistor: 160-Ω and 50-pF Capacitance 1.8 V to 3.3 V at 100 MHz)**

## 12 器件和文档支持

### 12.1 相关链接

下面的表格列出了快速访问链接。范围包括技术文档、支持与社区资源、工具和软件，并且可以快速访问样片或购买链接。

表 5. 相关链接

器件	产品文件夹	样片与购买	技术文档	工具与软件	支持与社区
LSF0101	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>
LSF0102	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>
LSF0108	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>

### 12.2 社区资源

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### 12.5 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 13 机械、封装和可订购信息

以下页中包括机械、封装和可订购信息。这些信息是针对指定器件可提供的最新数据。这些数据会在无通知且不对本文档进行修订的情况下发生改变。欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

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放大器和线性器件	<a href="http://www.ti.com.cn/amplifiers">www.ti.com.cn/amplifiers</a>	计算机及周边	<a href="http://www.ti.com.cn/computer">www.ti.com.cn/computer</a>
数据转换器	<a href="http://www.ti.com.cn/dataconverters">www.ti.com.cn/dataconverters</a>	消费电子	<a href="http://www.ti.com.cn/consumer-apps">www.ti.com.cn/consumer-apps</a>
DLP® 产品	<a href="http://www.dlp.com">www.dlp.com</a>	能源	<a href="http://www.ti.com.cn/energy">www.ti.com.cn/energy</a>
DSP - 数字信号处理器	<a href="http://www.ti.com.cn/dsp">www.ti.com.cn/dsp</a>	工业应用	<a href="http://www.ti.com.cn/industrial">www.ti.com.cn/industrial</a>
时钟和计时器	<a href="http://www.ti.com.cn/clockandtimers">www.ti.com.cn/clockandtimers</a>	医疗电子	<a href="http://www.ti.com.cn/medical">www.ti.com.cn/medical</a>
接口	<a href="http://www.ti.com.cn/interface">www.ti.com.cn/interface</a>	安防应用	<a href="http://www.ti.com.cn/security">www.ti.com.cn/security</a>
逻辑	<a href="http://www.ti.com.cn/logic">www.ti.com.cn/logic</a>	汽车电子	<a href="http://www.ti.com.cn/automotive">www.ti.com.cn/automotive</a>
电源管理	<a href="http://www.ti.com.cn/power">www.ti.com.cn/power</a>	视频和影像	<a href="http://www.ti.com.cn/video">www.ti.com.cn/video</a>
微控制器 (MCU)	<a href="http://www.ti.com.cn/microcontrollers">www.ti.com.cn/microcontrollers</a>		
RFID 系统	<a href="http://www.ti.com.cn/rfidsys">www.ti.com.cn/rfidsys</a>		
OMAP应用处理器	<a href="http://www.ti.com/omap">www.ti.com/omap</a>		
无线连通性	<a href="http://www.ti.com.cn/wirelessconnectivity">www.ti.com.cn/wirelessconnectivity</a>	德州仪器在线技术支持社区	<a href="http://www.deyisupport.com">www.deyisupport.com</a>

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**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LSF0101DRYR	ACTIVE	SON	DRY	6	5000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	VD	<a href="#">Samples</a>
LSF0102DCTR	ACTIVE	SM8	DCT	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	NG2 (S ~ Y)	<a href="#">Samples</a>
LSF0102DCUR	ACTIVE	VSSOP	DCU	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU   CU SN	Level-1-260C-UNLIM	-40 to 125	(G2 ~ NG2P ~ NG2S) NY	<a href="#">Samples</a>
LSF0102DQER	ACTIVE	X2SON	DQE	8	5000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	RV	<a href="#">Samples</a>
LSF0102YZTR	ACTIVE	DSBGA	YZT	8	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 125	RV	<a href="#">Samples</a>
LSF0108PWR	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU SN	Level-1-260C-UNLIM	-40 to 125	LSF0108	<a href="#">Samples</a>
LSF0108RKS	ACTIVE	VQFN	RKS	20	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	LSF0108	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSELETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=100ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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**TAPE AND REEL INFORMATION**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LSF0101DRYR	SON	DRY	6	5000	180.0	9.5	1.15	1.6	0.75	4.0	8.0	Q1
LSF0102DCTR	SM8	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
LSF0102DCUR	VSSOP	DCU	8	3000	180.0	9.0	2.05	3.3	1.0	4.0	8.0	Q3
LSF0102DCUR	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
LSF0102DQER	X2SON	DQE	8	5000	180.0	9.5	1.15	1.6	0.5	4.0	8.0	Q1
LSF0102YZTR	DSBGA	YZT	8	3000	180.0	8.4	1.02	2.02	0.75	4.0	8.0	Q1
LSF0108PWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1
LSF0108RKSR	VQFN	RKS	20	3000	177.8	12.4	2.73	4.85	1.03	4.0	12.0	Q1

**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LSF0101DRYR	SON	DRY	6	5000	184.0	184.0	19.0
LSF0102DCTR	SM8	DCT	8	3000	182.0	182.0	20.0
LSF0102DCUR	VSSOP	DCU	8	3000	182.0	182.0	20.0
LSF0102DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
LSF0102DQER	X2SON	DQE	8	5000	184.0	184.0	19.0
LSF0102YZTR	DSBGA	YZT	8	3000	182.0	182.0	20.0
LSF0108PWR	TSSOP	PW	20	2000	364.0	364.0	27.0
LSF0108RKS	VQFN	RKS	20	3000	202.0	201.0	28.0



DCU (S-PDSO-G8)

PLASTIC SMALL OUTLINE PACKAGE (DIE DOWN)



4210064/C 04/12

- NOTES:
- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Publication IPC-7351 is recommended for alternate designs.
  - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
  - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

## GENERIC PACKAGE VIEW

**DRY 6**

**USON - 0.6 mm max height**

PLASTIC SMALL OUTLINE - NO LEAD



Images above are just a representation of the package family, actual package may vary.  
Refer to the product data sheet for package details.

4207181/G



NOTES:

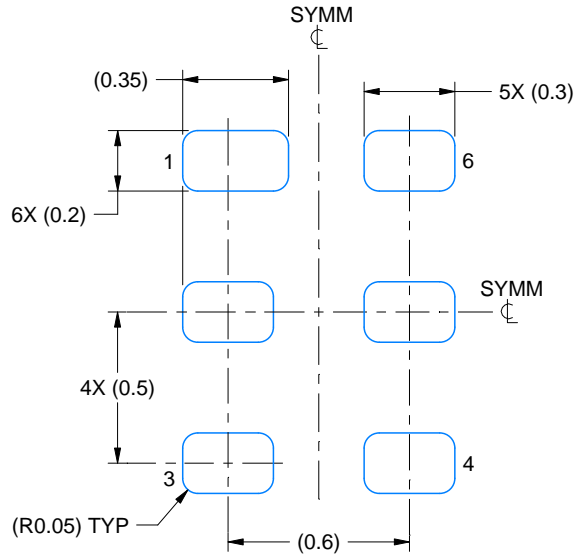
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

# EXAMPLE BOARD LAYOUT

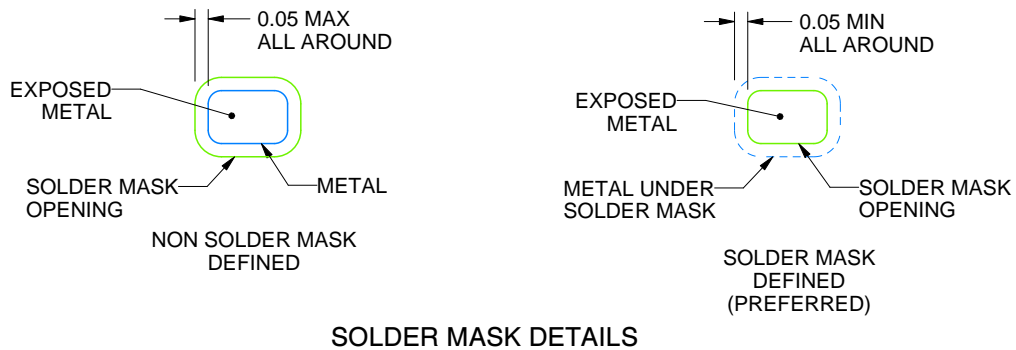
DRY0006A

USON - 0.6 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



**LAND PATTERN EXAMPLE**  
 1:1 RATIO WITH PKG SOLDER PADS  
 EXPOSED METAL SHOWN  
 SCALE:40X



**SOLDER MASK DETAILS**

4222894/A 01/2018

NOTES: (continued)

3. For more information, see QFN/SON PCB application report in literature No. SLUA271 ([www.ti.com/lit/slua271](http://www.ti.com/lit/slua271)).

# EXAMPLE STENCIL DESIGN

DRY0006A

USON - 0.6 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER PASTE EXAMPLE  
BASED ON 0.075 - 0.1 mm THICK STENCIL  
SCALE:40X

4222894/A 01/2018

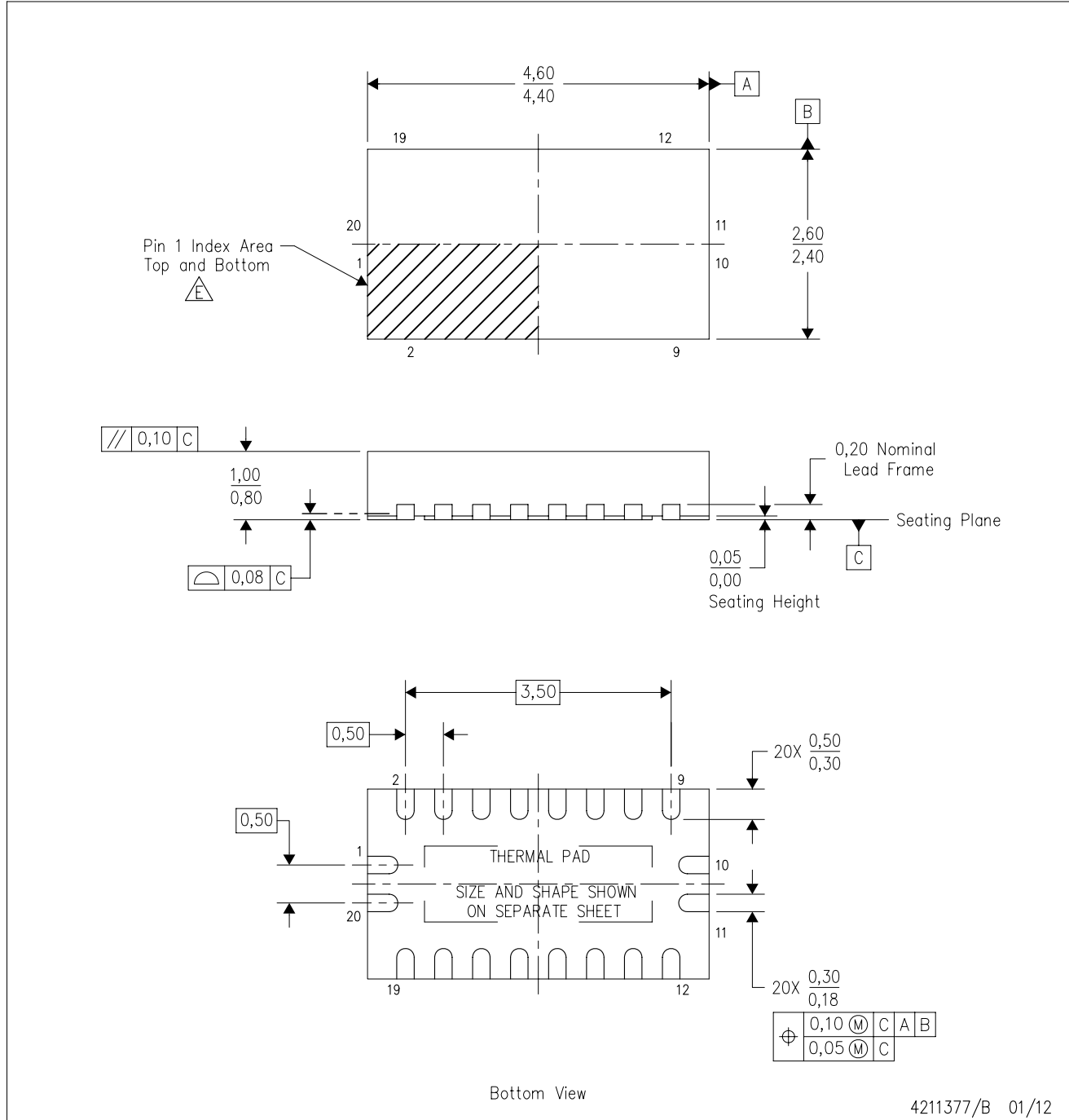
NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



RKS (R-PVQFN-N20)

PLASTIC QUAD FLATPACK NO-LEAD



- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
  - B. This drawing is subject to change without notice.
  - C. QFN (Quad Flatpack No-Lead) package configuration.
  - D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
  - E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- △ Pin 1 identifiers are located on both top and bottom of the package and within the zone indicated. The Pin 1 identifiers are either a molded, marked, or metal feature.

# THERMAL PAD MECHANICAL DATA

RKS (R-PVQFN-N20)

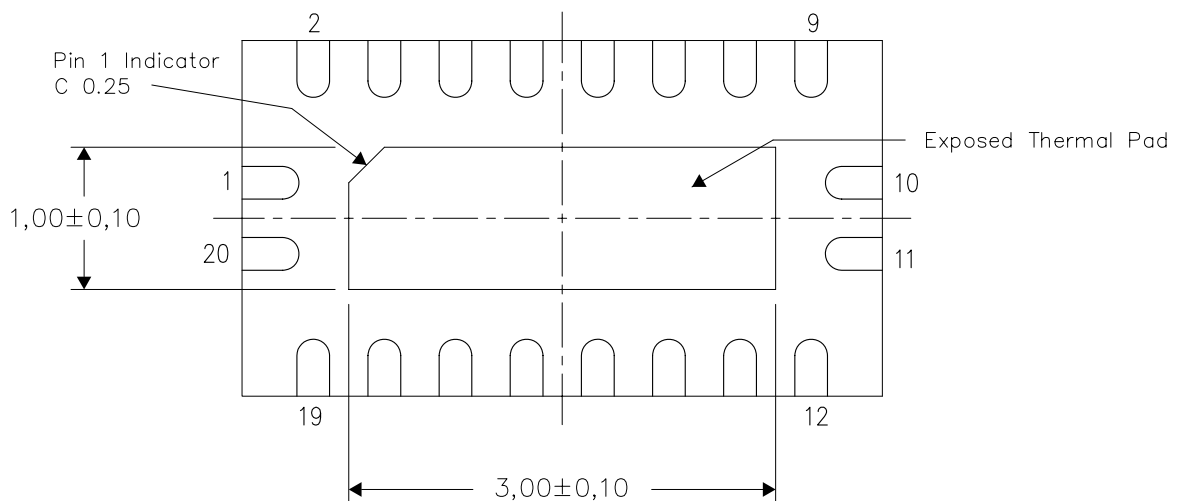
PLASTIC QUAD FLATPACK NO-LEAD

## THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at [www.ti.com](http://www.ti.com).

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

Exposed Thermal Pad Dimensions

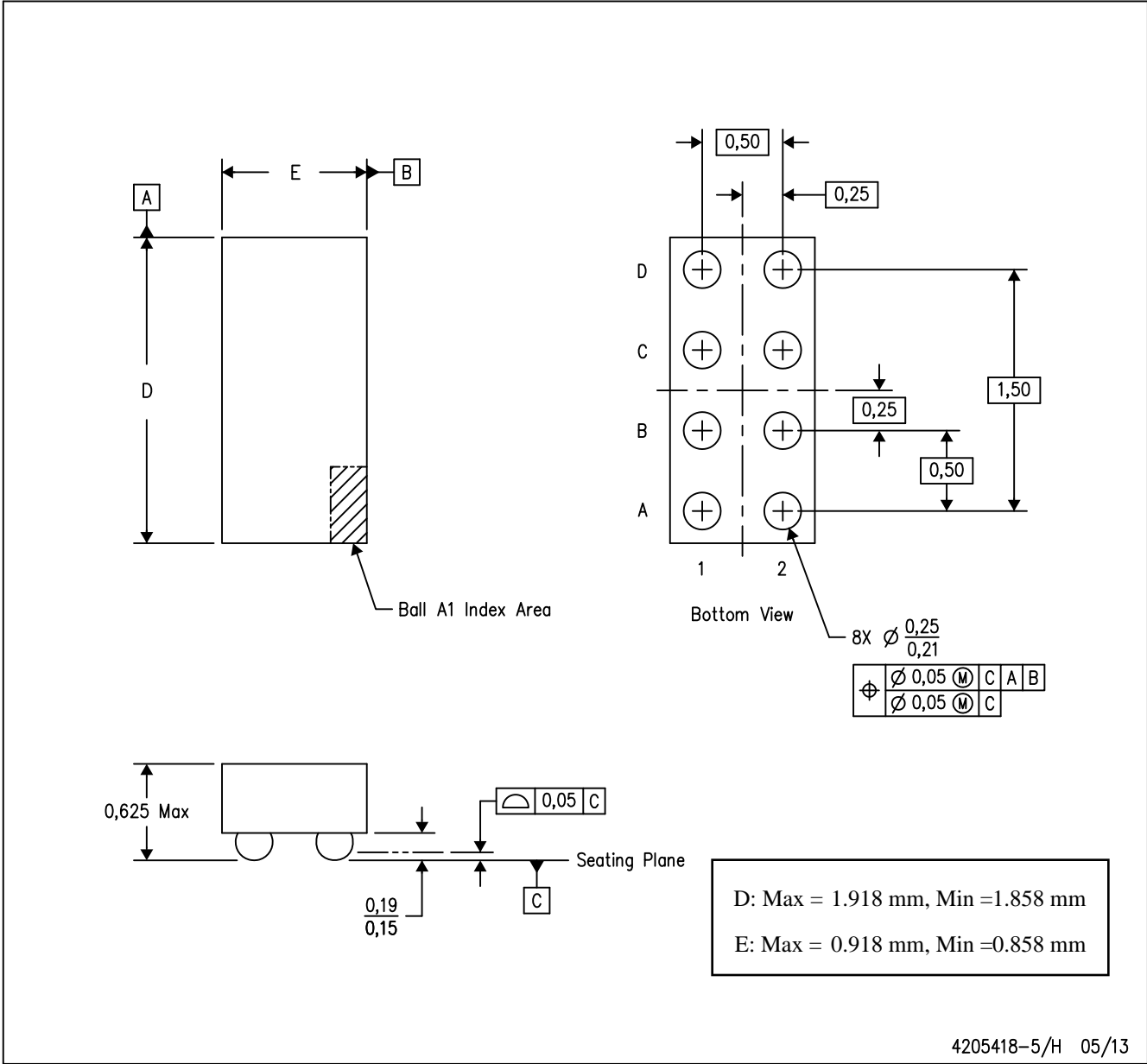
4211394/B 01/12

NOTE: All linear dimensions are in millimeters

**MECHANICAL DATA**

YZT (R-XBGA-N8)

DIE-SIZE BALL GRID ARRAY



- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
  - B. This drawing is subject to change without notice.
  - C. NanoFree™ package configuration.

NanoFree is a trademark of Texas Instruments.

PW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



4040064-5/G 02/11

- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
  - B. This drawing is subject to change without notice.
  - C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
  - D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
  - E. Falls within JEDEC MO-153

PW (R-PDSO-G20)

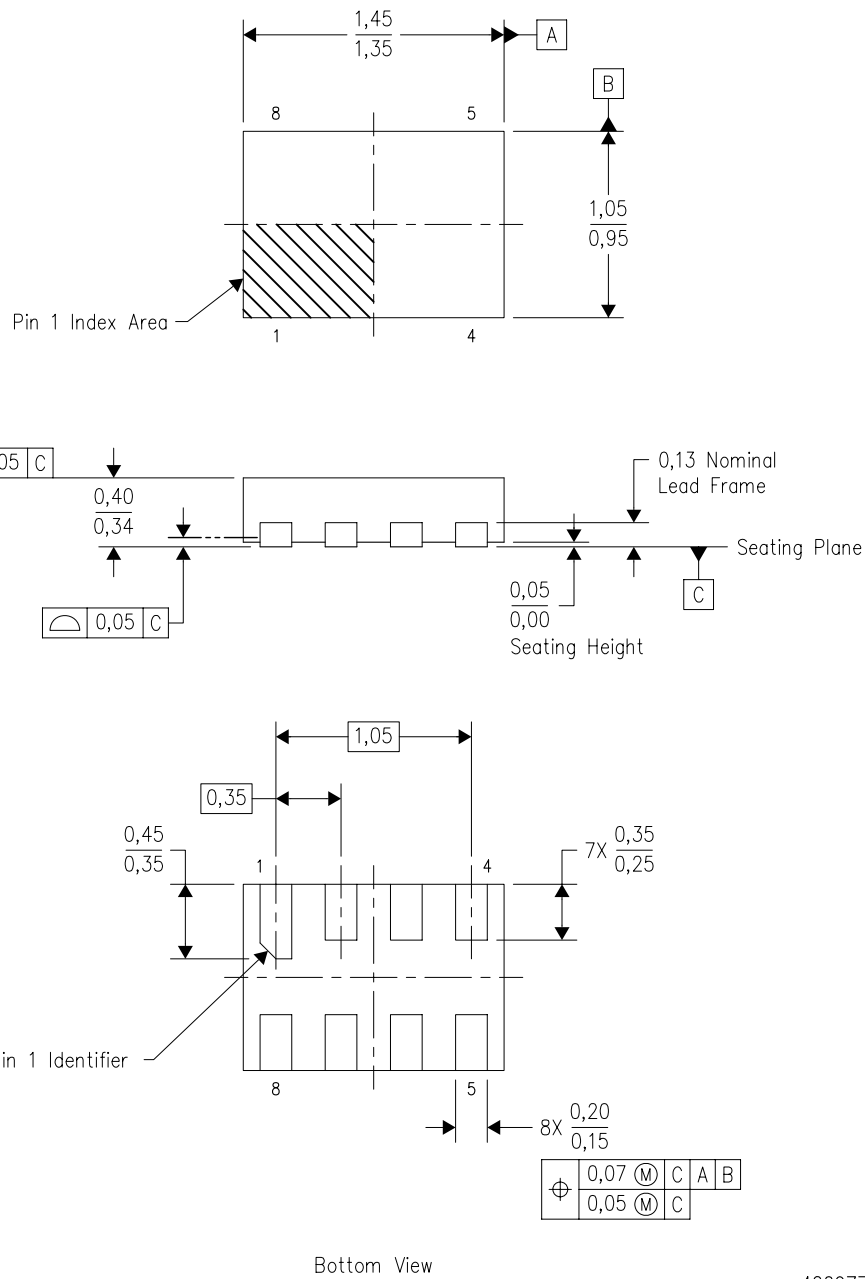
PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Publication IPC-7351 is recommended for alternate design.
  - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
  - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

DQE (R-PX2SON-N8)

PLASTIC SMALL OUTLINE NO-LEAD

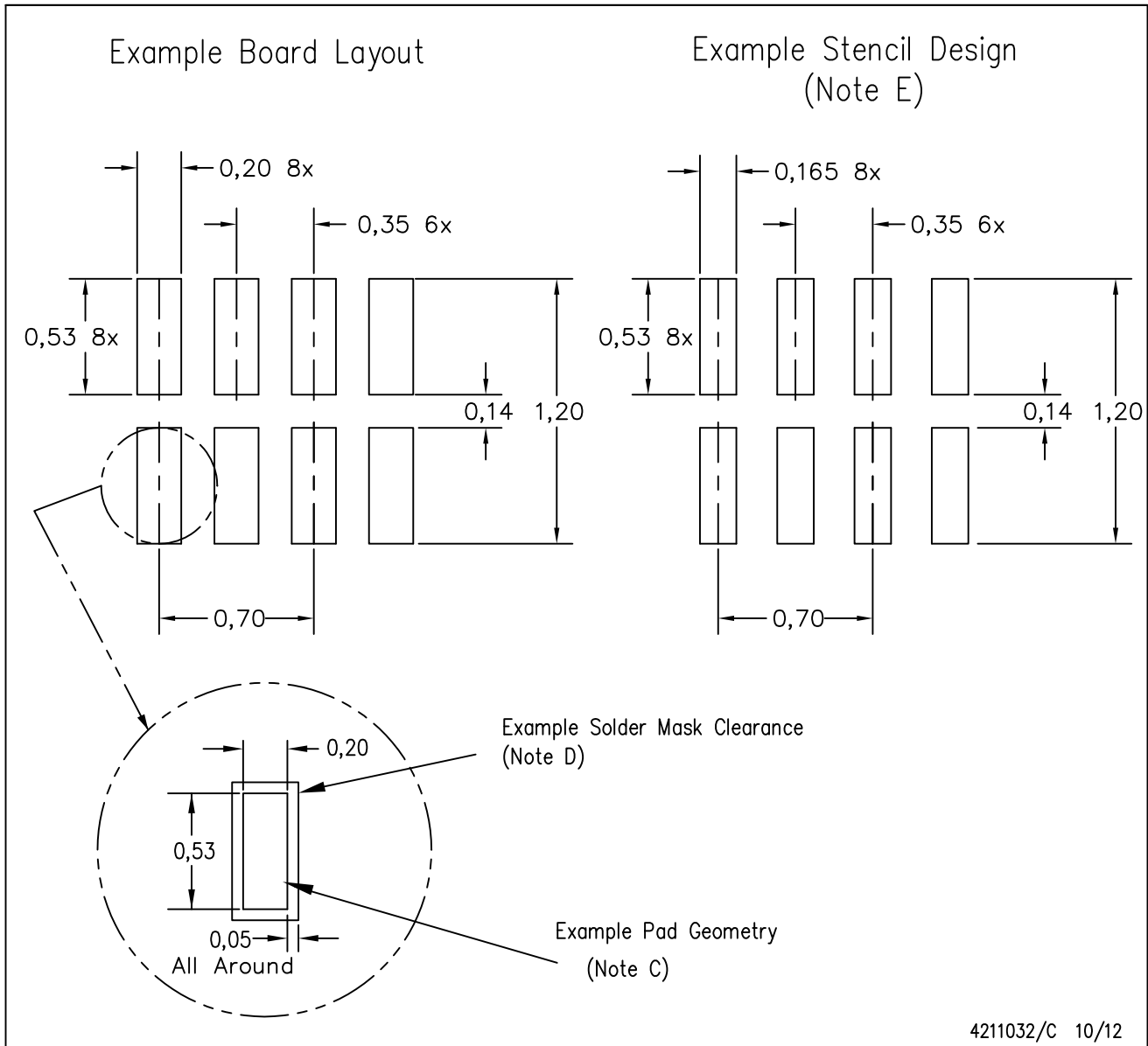


4209779/B 10/2008

- NOTES:
- All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
  - This drawing is subject to change without notice.
  - SON (Small Outline No-Lead) package configuration.
  - This package complies to JEDEC MO-287 variation X2EAF.

DQE (R-PX2SON-N8)

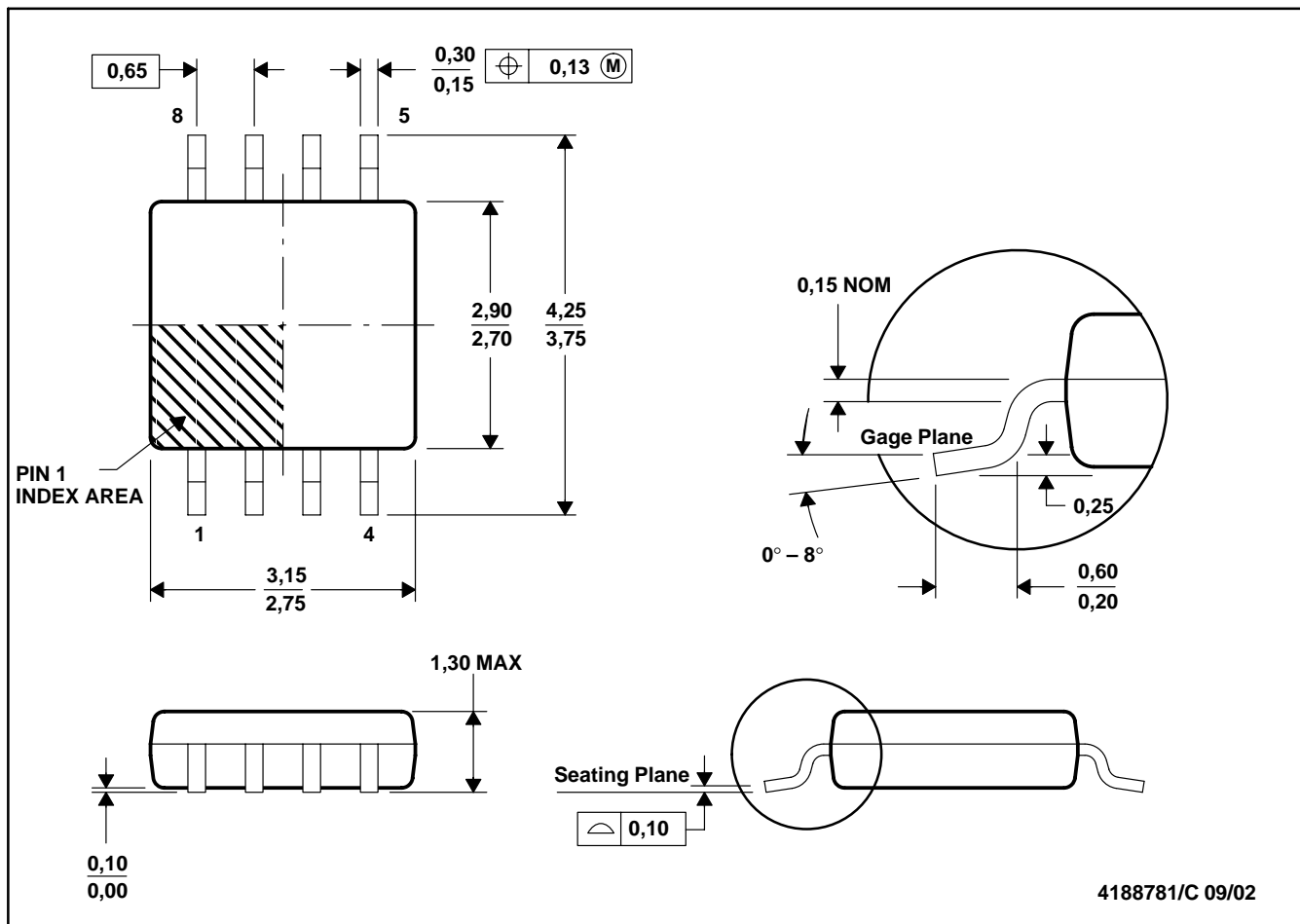
PLASTIC SMALL OUTLINE NO-LEAD



- NOTES:
- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Publication IPC-7351 is recommended for alternate designs.
  - D. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.  
If 2 mil solder mask is outside PCB vendor capability, it is advised to omit solder mask.
  - E. Maximum stencil thickness 0,1016 mm (4 mils). All linear dimensions are in millimeters.
  - F. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
  - G. Over-printing land for acceptable area ratio is not viable due to land width and bridging potential. Customer may further reduce side aperture dimensions if stencil manufacturing process allows for sufficient release at smaller opening.
  - H. Suggest stencils cut with lasers such as Fiber Laser that produce the greatest positional accuracy.
  - I. Component placement force should be minimized to prevent excessive paste block deformation.

DCT (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



- NOTES: A. All linear dimensions are in millimeters.  
 B. This drawing is subject to change without notice.  
 C. Body dimensions do not include mold flash or protrusion  
 D. Falls within JEDEC MO-187 variation DA.



DCT (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Publication IPC-7351 is recommended for alternate designs.
  - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525.
  - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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